

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Y. Zhang et al.

Application No.: 10/730,891

Confirmation No.: 5178

Filed: December 10, 2003

Art Unit: 2112

For: Method of Etching Dual Pre-Doped Polysilicon
Gate Stacks Using Carbon-Containing Gaseous
Additions

Examiner: A. B. Mustapha

AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Office Action dated January 10 2007, please amend the above-identified U.S. patent application as follows:

Amendments to the Abstract begin on page 2 of this paper

Amendments to the Specification begin on page 3 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks/Arguments begin on page 5 of this paper.